Title (en)
    PROCESS FOR PRODUCING POLYCRYSTALLINE SILICON

Title (de)
    VERFAHREN ZUR HERSTELLUNG VON POLYKRISTALLINEM SILICIUM

Title (fr)
    PROCÉDÉ DE PRODUCTION DE SILICIUM POLYCRISTALLIN

Publication
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Application
    EP 14786183 A 20141017

Priority
    • DE 102013221826 A 20131028
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Abstract (en)
    [origin: WO2015062880A1] The invention relates to a method for producing polycrystalline silicon, comprising a deposition of polycrystalline
    silicon on a carrier body in order to obtain a polycrystalline silicon rod, or a deposition of polycrystalline silicon on silicon particles in order to obtain
    polycrystalline silicon granules, wherein each deposition takes place in a reactor located in a class 1-100 000 cleanroom into which filtered air is
    directed. For filtration, said air first passes through at least one filter that removes particles greater than or equal to 1 μm, and subsequently passes
    through a HEPA filter that removes particles smaller than 1 μm.

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